



IFW

PATENT
Customer No. 22,852
Attorney Docket No. 4208.0204

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	
)	
Takayuki WATANABE et al.)	Group Art Unit: 2812
)	
Application No.: 10/501,349)	Examiner: Not Yet Assigned
)	
Filed: July 15, 2004)	
)	
For: COMPOUND SEMICONDUCTOR)	Confirmation No.: 7885
MULTILAYER STRUCTURE, HALL)	
DEVICE, AND HALL DEVICE)	
MANUFACTURING METHOD)	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of the Examiner the documents on the attached listing. This Information Disclosure Statement is being filed before the mailing date of a first Office Action on the merits for the above-referenced application.

Copies of the listed foreign and non-patent literature documents are attached.

Copies of the U.S. patent publications are not enclosed.

This application is a § 371 of PCT/JP03/00291, filed January 15, 2003. The listed documents were cited in the Specification, in the International Search Report and International Preliminary Examination Report.

Applicants respectfully request that the Examiner consider the listed documents and indicate that they were considered by making appropriate notations on the attached form.

English language abstracts are provided for all cited Japanese patent document.

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of such documents.

Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

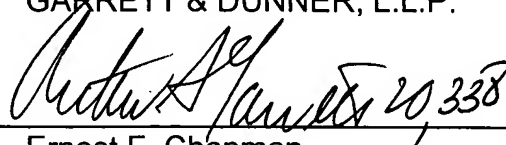
If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,
GARRETT & DUNNER, L.L.P.

Dated: November 16, 2004

By:


Ernest F. Chapman
Reg. No. 25,961

IDS Form PTO/SB/08: Substitute for form 1449A/PTO <h2 style="text-align: center; margin: 10px 0;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center; font-size: small;">(Use as many sheets as necessary)</p>				Complete if Known	
Application Number		10/501,349			
Filing Date		July 15, 2004			
First Named Inventor		Takayuki WATANABE et al.			
Art Unit		2812			
Examiner Name		Unassigned			
Attorney Docket Number		4208.0204			

OIPE
NOV 16 2004
PATENT & TRADEMARK OFFICE

Sheet	1	of	1
-------	---	----	---

U.S. PATENTS AND PUBLISHED U.S. PATENT APPLICATIONS					
Examiner Initials	Cite No. ¹	Document Number	Issue or Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US 5,430,310-	July 4, 1995	Ichiro Shibasaki et al.	
		US 2001/0055002 A1	Dec. 27, 2001	Michiko ENDO	
		US 2002/0009192 A1	Jan. 24, 2002	Futoshi Nakamura	

Note: Copies of the U.S. Patent Documents are not Required in IDS filed after October 21, 2004

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Translation ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		Japan P3069545 Japan 10-233539	5/19/2000 2/9/1998	Asahi Chem Ind Co Ltd		English Abstract
		Japan 2793440 Japan 06-077556	6/19/1998 3/18/1994	Asahi Chem Ind Co Ltd		English Abstract
		Japan 09-116207	5/2/1997	Asahi Chem Ind Co Ltd		English Abstract
		Japan 05-297084	11/12/1993	Toyoto Motor Corp Nippon Autom KK		English Abstract
		Japan 2000-183424	6/3/2000	Hitachi Cable Ltd		English Abstract
		Japan 07-283390	10/27/1995	Asahi Chem Ind Co Ltd		English Abstract
		Japan 2001-352369	12/21/2001	NEC Saitama Ltd		English Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation ⁶
		N. Kuze et al., "Molecular beam epitaxial growth of InAs/AlGaAsSb deep quantum well structures on GaAs substrates," J. Vac. Sci. Technol. B 16(5), Sep/Oct 1998, American Vacuum Society, pp. 2644-2649	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.